

## Power MOSFET



N-Channel MOSFET

### FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

| PRODUCT SUMMARY           |                            |
|---------------------------|----------------------------|
| $V_{DS}$ (V)              | 600                        |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ 2.2 |
| $Q_g$ max. (nC)           | 31                         |
| $Q_{gs}$ (nC)             | 4.6                        |
| $Q_{gd}$ (nC)             | 17                         |
| Configuration             | Single                     |

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

| ORDERING INFORMATION            |                |
|---------------------------------|----------------|
| Package                         | TO-220AB       |
| Lead (Pb)-free                  | IRFBC30PbF     |
| Lead (Pb)-free and halogen-free | IRFBC30PbF-BE3 |

| ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted) |                                  |                                   |                     |                  |
|---|----------------------------------|-----------------------------------|---------------------|------------------|
| PARAMETER   | SYMBOL                           | LIMIT                             | UNIT                |                  |
| Drain-source voltage  | $V_{DS}$                         | 600                               | V                   |                  |
| Gate-source voltage   | $V_{GS}$                         | $\pm 20$                          |                     |                  |
| Continuous drain current  | $V_{GS}$ at 10 V                 | $T_C = 25\text{ }^\circ\text{C}$  | 3.6                 | A                |
|   |                                  | $T_C = 100\text{ }^\circ\text{C}$ | 2.3                 |                  |
| Pulsed drain current <sup>a</sup>   | $I_{DM}$                         | 14                                |                     |                  |
| Linear derating factor  |                                  | 0.59                              | W/ $^\circ\text{C}$ |                  |
| Single pulse avalanche energy <sup>b</sup>  | $E_{AS}$                         | 290                               | mJ                  |                  |
| Repetitive avalanche current <sup>a</sup>   | $I_{AR}$                         | 3.6                               | A                   |                  |
| Repetitive avalanche energy <sup>a</sup>  | $E_{AR}$                         | 7.4                               | mJ                  |                  |
| Maximum power dissipation   | $T_C = 25\text{ }^\circ\text{C}$ | $P_D$                             | 74                  | W                |
| Peak diode recovery dV/dt <sup>c</sup>  |                                  | dV/dt                             | 3.0                 | V/ns             |
| Operating junction and storage temperature range                                      | $T_J, T_{stg}$                   |                                   | -55 to +150         | $^\circ\text{C}$ |
| Soldering recommendations (peak temperature) <sup>d</sup>                             | For 10 s                         |                                   | 300                 |                  |
| Mounting torque   | 6-32 or M3 screw                 |                                   | 10                  | lbf · in         |
|   |                                  |                                   | 1.1                 | N · m            |

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 41\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 3.6\text{ A}$  (see fig. 12)
- $I_{SD} \leq 3.6\text{ A}$ ,  $dI/dt \leq 60\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case

| <b>THERMAL RESISTANCE RATINGS</b>   |            |      |      |      |
|-------------------------------------|------------|------|------|------|
| PARAMETER                           | SYMBOL     | TYP. | MAX. | UNIT |
| Maximum junction-to-ambient         | $R_{thJA}$ | -    | 62   | °C/W |
| Case-to-sink, flat, greased surface | $R_{thCS}$ | 0.50 | -    |      |
| Maximum junction-to-case (drain)    | $R_{thJC}$ | -    | 1.7  |      |

| <b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted) |                     |  |  |      |      |           |               |
|--|---------------------|--|--|------|------|-----------|---------------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS  |  | MIN. | TYP. | MAX.      | UNIT          |
| <b>Static</b>  |                     |  |  |      |      |           |               |
| Drain-source breakdown voltage   | $V_{DS}$            | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$  |  | 600  | -    | -         | V             |
| $V_{DS}$ temperature coefficient   | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$  |  | -    | 0.62 | -         | V/°C          |
| Gate-source threshold voltage  | $V_{GS(th)}$        | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$  |  | 2.0  | -    | 4.0       | V             |
| Gate-source leakage  | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$   |  | -    | -    | $\pm 100$ | nA            |
| Zero gate voltage drain current  | $I_{DSS}$           | $V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$   |  | -    | -    | 100       | $\mu\text{A}$ |
|  |                     | $V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$  |  | -    | -    | 500       |               |
| Drain-source on-state resistance   | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$   | $I_D = 2.2\text{ A}^b$   | -    | -    | 2.2       | $\Omega$      |
| Forward transconductance   | $g_{fs}$            | $V_{DS} = 100\text{ V}, I_D = 2.2\text{ A}^b$  |  | 2.5  | -    | -         | S             |
| <b>Dynamic</b>   |                     |  |  |      |      |           |               |
| Input capacitance  | $C_{iss}$           | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5   |  | -    | 660  | -         | $\mu\text{F}$ |
| Output capacitance   | $C_{oss}$           |  |  | -    | 86   | -         |               |
| Reverse transfer capacitance   | $C_{rss}$           |  |  | -    | 19   | -         |               |
| Total gate charge  | $Q_g$               | $V_{GS} = 10\text{ V}$   | $I_D = 3.6\text{ A}, V_{DS} = 360\text{ V}$ , see fig. 6 and 13 <sup>b</sup> | -    | -    | 31        | nC            |
| Gate-source charge   | $Q_{gs}$            |  |  | -    | -    | 4.6       |               |
| Gate-drain charge  | $Q_{gd}$            |  |  | -    | -    | 17        |               |
| Turn-on delay time   | $t_{d(on)}$         | $V_{DD} = 300\text{ V}, I_D = 3.6\text{ A}, R_g = 12\text{ }\Omega, R_D = 82\text{ }\Omega$ , see fig. 10 <sup>b</sup> |  | -    | 11   | -         | ns            |
| Rise time  | $t_r$               |  |  | -    | 13   | -         |               |
| Turn-off delay time  | $t_{d(off)}$        |  |  | -    | 35   | -         |               |
| Fall time  | $t_f$               |  |  | -    | 14   | -         |               |
| Gate input resistance  | $R_g$               | $f = 1\text{ MHz}$ , open drain  |  | 0.5  | -    | 4.9       | $\Omega$      |
| Internal drain inductance  | $L_D$               | Between lead, 6 mm (0.25") from package and center of die contact  |  | -    | 4.5  | -         | nH            |
| Internal source inductance   | $L_S$               |  |  | -    | 7.5  | -         |               |
| <b>Drain-Source Body Diode Characteristics</b>                                     |                     |  |  |      |      |           |               |
| Continuous source-drain diode current  | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode  |  | -    | -    | 3.6       | A             |
| Pulsed diode forward current <sup>a</sup>  | $I_{SM}$            |  |  | -    | -    | 14        |               |
| Body diode voltage   | $V_{SD}$            | $T_J = 25\text{ }^\circ\text{C}, I_S = 3.6\text{ A}, V_{GS} = 0\text{ V}^b$  |  | -    | -    | 1.6       | V             |
| Body diode reverse recovery time   | $t_{rr}$            | $T_J = 25\text{ }^\circ\text{C}, I_F = 3.6\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$                               |  | -    | 370  | 810       | ns            |
| Body diode reverse recovery charge   | $Q_{rr}$            |  |  | -    | 2.0  | 4.2       | $\mu\text{C}$ |
| Forward turn-on time   | $t_{on}$            | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )  |  |      |      |           |               |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)  
 b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

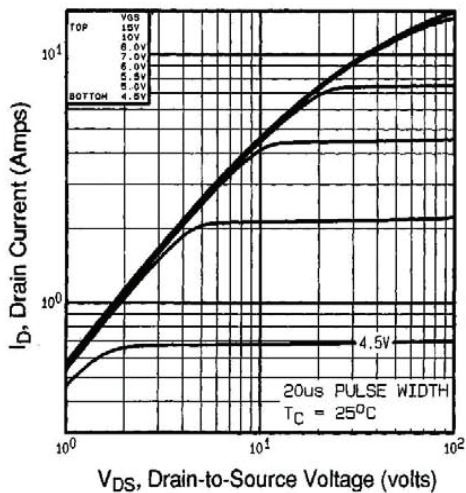


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

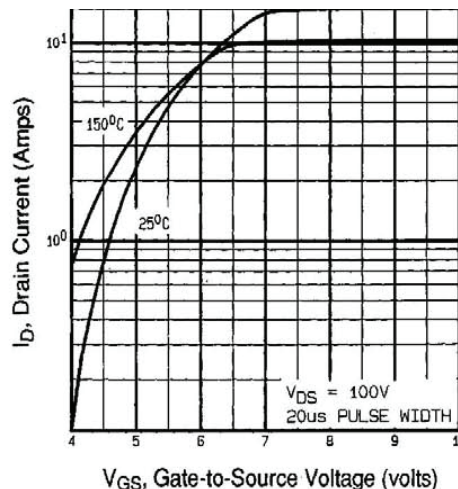


Fig. 3 - Typical Transfer Characteristics

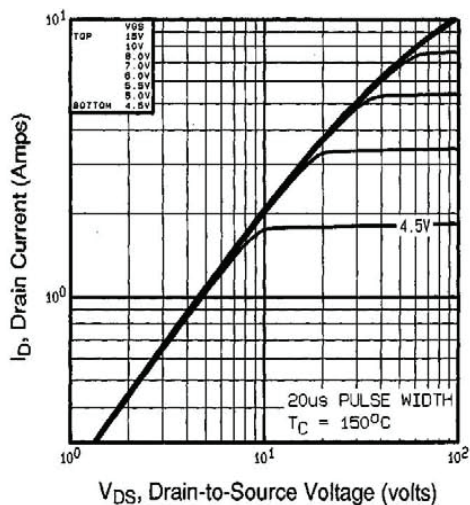


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

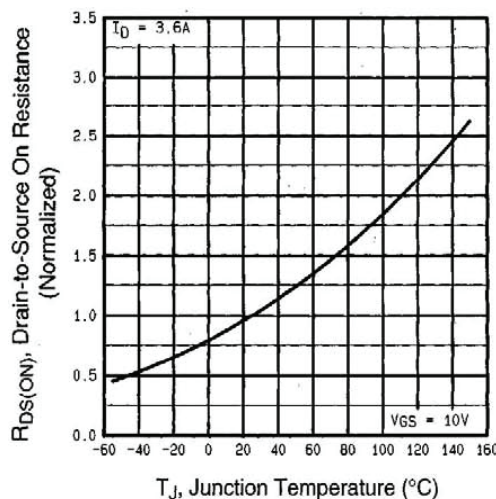


Fig. 4 - Normalized On-Resistance vs. Temperature

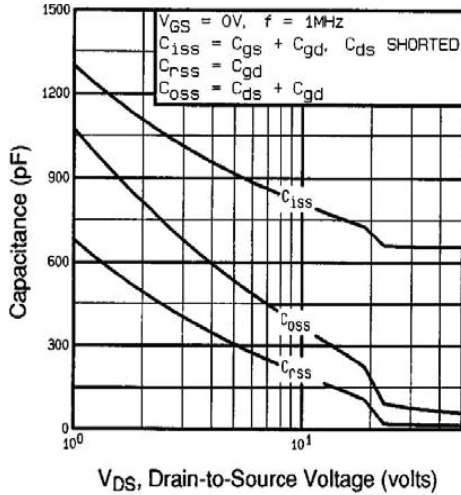


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

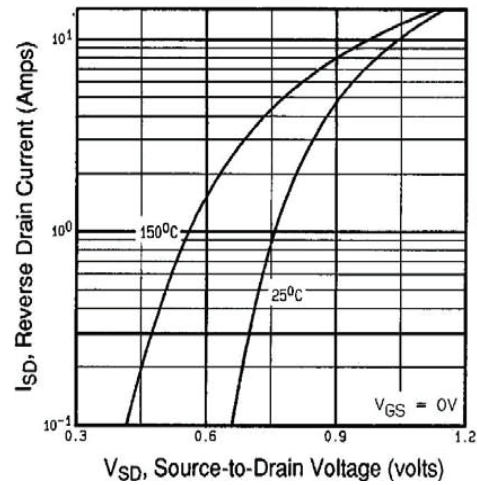


Fig. 7 - Typical Source-Drain Diode Forward Voltage

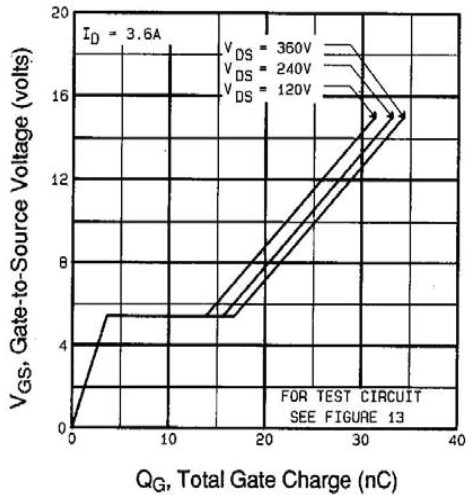


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

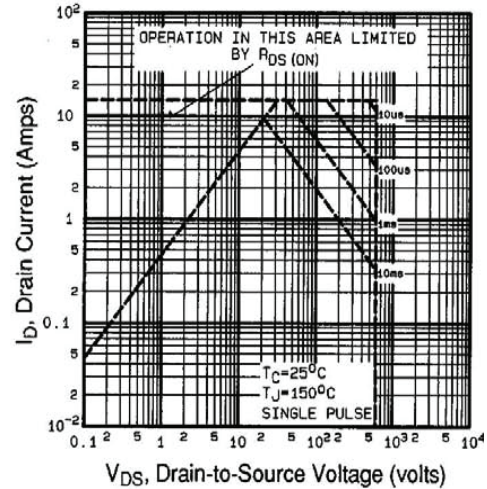


Fig. 8 - Maximum Safe Operating Area

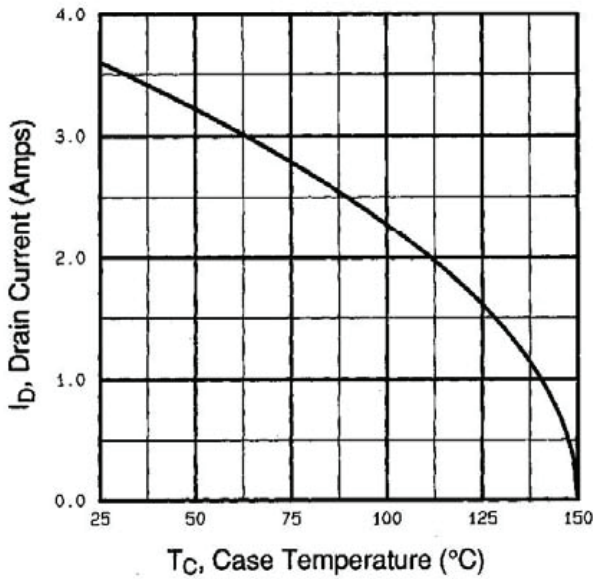


Fig. 9 - Maximum Drain Current vs. Case Temperature

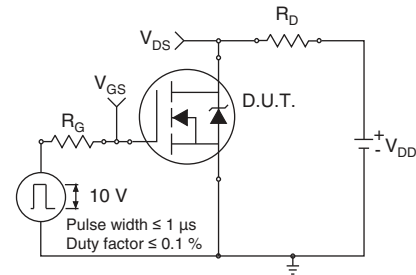


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

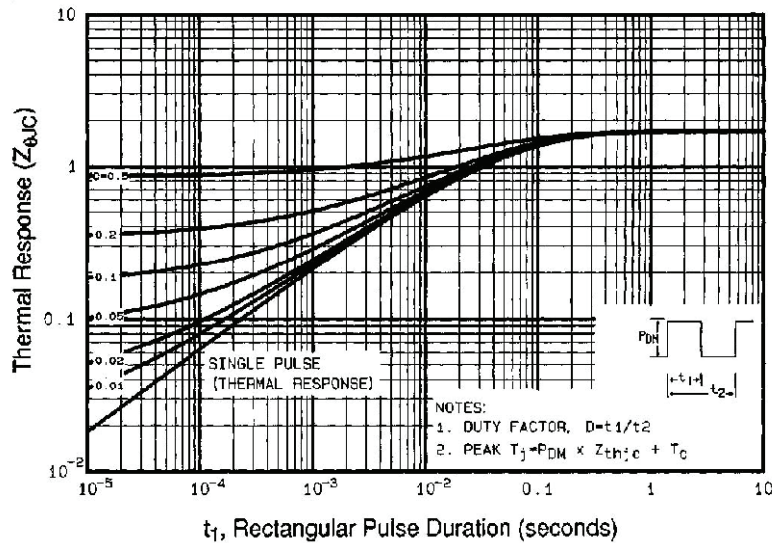


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

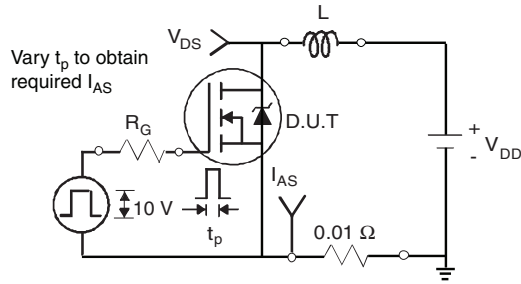


Fig. 12a - Unclamped Inductive Test Circuit

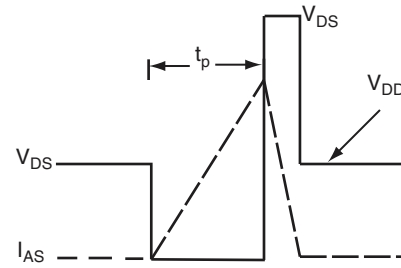


Fig. 12b - Unclamped Inductive Waveforms

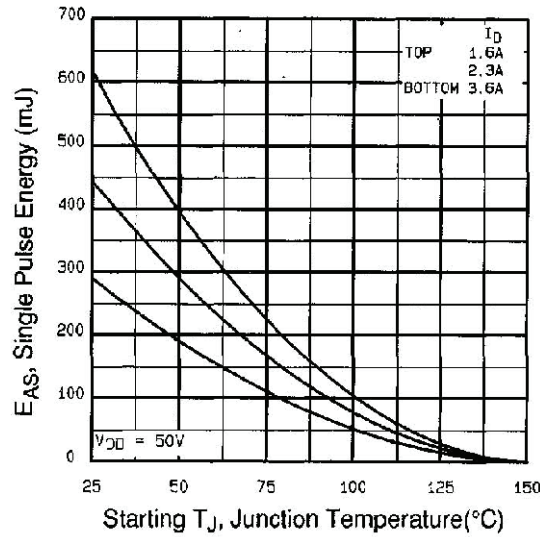


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

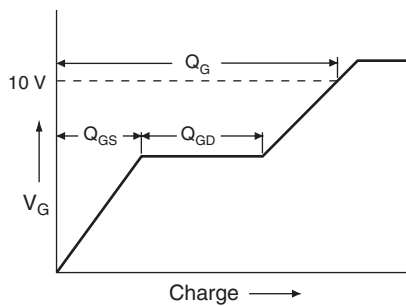


Fig. 13a - Basic Gate Charge Waveform

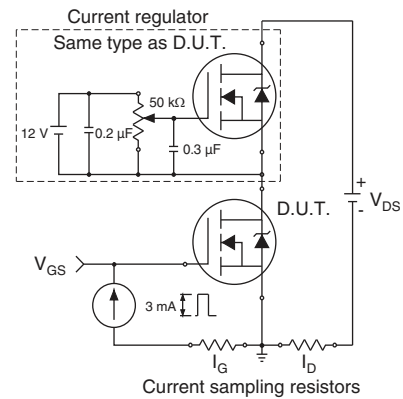
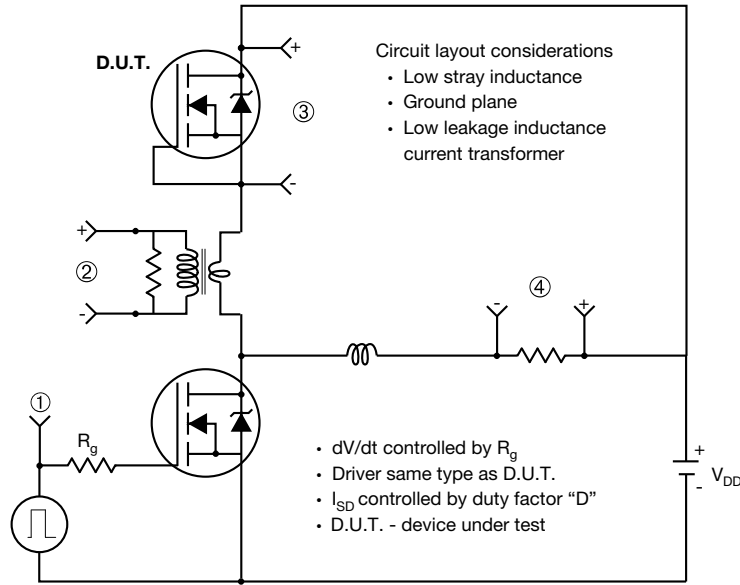


Fig. 13b - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**



**Note**  
a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**

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# TO-220-1



| DIM. | MILLIMETERS |       | INCHES |       |
|------|-------------|-------|--------|-------|
|      | MIN.        | MAX.  | MIN.   | MAX.  |
| A    | 4.24        | 4.65  | 0.167  | 0.183 |
| b    | 0.69        | 1.02  | 0.027  | 0.040 |
| b(1) | 1.14        | 1.78  | 0.045  | 0.070 |
| c    | 0.36        | 0.61  | 0.014  | 0.024 |
| D    | 14.33       | 15.85 | 0.564  | 0.624 |
| E    | 9.96        | 10.52 | 0.392  | 0.414 |
| e    | 2.41        | 2.67  | 0.095  | 0.105 |
| e(1) | 4.88        | 5.28  | 0.192  | 0.208 |
| F    | 1.14        | 1.40  | 0.045  | 0.055 |
| H(1) | 6.10        | 6.71  | 0.240  | 0.264 |
| J(1) | 2.41        | 2.92  | 0.095  | 0.115 |
| L    | 13.36       | 14.40 | 0.526  | 0.567 |
| L(1) | 3.33        | 4.04  | 0.131  | 0.159 |
| Ø P  | 3.53        | 3.94  | 0.139  | 0.155 |
| Q    | 2.54        | 3.00  | 0.100  | 0.118 |

ECN: E21-0621-Rev. D, 04-Nov-2021  
 DWG: 6031

**Note**

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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